BLF2425M6L180P; BLF2425M6LS180P

Power LDMOS transistor

Rev. 3 — 12 July 2013

Product data sheet

1. Product profile

1.1 General description

180 W LDMOS power transistor for various applications such as ISM and industrial heating at frequencies from 2400 MHz to 2500 MHz.

Table 1. Typical performance

RF performance at $T_{\rm case}$ = 25 °C in a common source class-AB production test circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	Gp	η _D
	(MHz)	(mA)	(V)	(W)	(dB)	(%)
CW	2450	10	28	180	13.3	53.5

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (2400 MHz to 2500 MHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for CW applications in the 2400 MHz to 2500 MHz frequency range such as ISM and industrial heating.



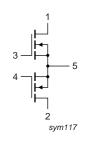
2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF2425	M6L180P (SOT539A)			
1	drain1			
2	drain2		1 2	1 ال
3	gate1		5	3
4	gate2		3 4	5
5	source	<u>[1]</u>		4
				' <u> </u>
				2 sym117

BLF242	5M6LS180P (SOT539B)		
1	drain1		
2	drain2		کے
3	gate1		Ļ
4	gate2		_
5	source	<u>[1]</u>	





[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package		
	Name	Description	Version	
BLF2425M6L180P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A	
BLF2425M6LS180P	-	earless flanged balanced ceramic package; 4 leads	SOT539B	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	$T_{case} = 80 ^{\circ}C; P_{L} = 180 W$	0.38	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C per section; unless otherwise specified.

,	-					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.44 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 144 \text{ mA}$	1.4	1.8	2.4	V
I _{DSS}	drain leakage current	$V_{GS} = 0 V$				
		$V_{DS} = 28 \text{ V}$	-	-	3	μΑ
		$V_{DS} = 65 \text{ V}$	-	-	5	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	24	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	300	nΑ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.2 \text{ A}$	-	10	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5 \text{ A}$	-	0.1	-	Ω

Table 7. RF characteristics

Test signal: CW; f = 2450 MHz; $V_{DS} = 28$ V; $I_{Dq} = 10$ mA; $T_{case} = 25$ °C unless otherwise specified in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L} = 180 \text{ W}$	11.0	13.3	-	dB
η_{D}	drain efficiency	$P_{L} = 180 \text{ W}$	50	53.5	-	%
RLin	input return loss	$P_{L} = 180 \text{ W}$	-	-15	-9	dB

7. Test information

7.1 Ruggedness in class-AB operation

The BLF2425M6L180P and BLF2425M6LS180P are capable of withstanding a load mismatch corresponding to VSWR = 5:1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 10 \text{ mA}$; $P_L = 180 \text{ W}$ (CW); f = 2450 MHz.

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data. Typical values per section.

 Z_{S} and Z_{L} defined in <u>Figure 1</u>.

f	Z _S	Z _L
(MHz)	(Ω)	(Ω)
2400	5.9 – j8.0	2.8 – j3.1
2450	8.4 – j7.6	2.5 – j3.1
2500	10.6 – j5.8	2.3 – j3.0

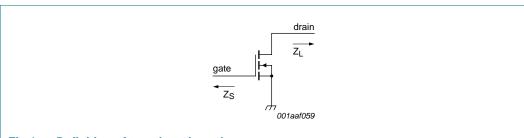
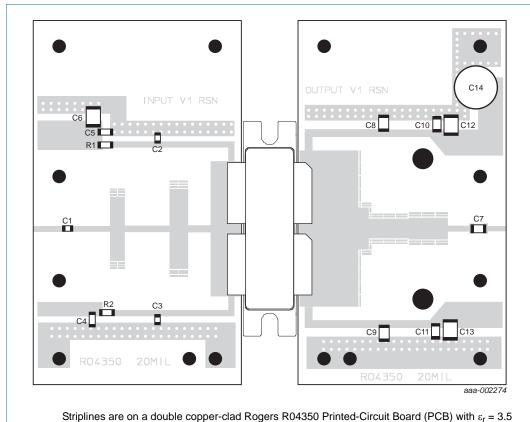


Fig 1. Definition of transistor impedance

7.3 Test circuit



and thickness = 0.508 mm.

See Table 9 for list of components.

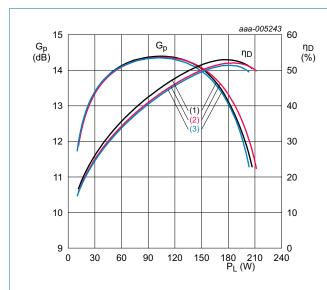
Fig 2. Component layout for test circuit

Table 9. List of components For test circuit, see Figure 2.

ComponentDescriptionValueRemarkC1, C2, C3multilayer ceramic chip capacitor15 pF[1]C4, C5, C10, C11multilayer ceramic chip capacitor220 nFSMDC6, C12, C13multilayer ceramic chip capacitor4.7 μFC7multilayer ceramic chip capacitor39 pF[2]	arks
C4, C5, C10, C11 multilayer ceramic chip capacitor 220 nF SMD C6, C12, C13 multilayer ceramic chip capacitor 4.7 μF	
C6, C12, C13 multilayer ceramic chip capacitor 4.7 μF	
	1206
C7 multilayer ceramic chip capacitor 39 pF [2]	
C8, C9 multilayer ceramic chip capacitor 6.8 pF	
C14 electrolytic capacitor 220 µF, 63 V	
R1, R2 chip resistor 6.2Ω SMD	1206

- [1] American technical ceramics type 100A or capacitor of same quality.
- [2] American technical ceramics type 800B or capacitor of same quality.
- [3] American technical ceramics type 100B or capacitor of same quality.

7.4 Graphical data



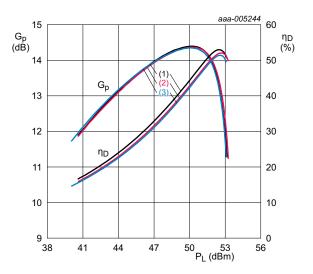
 $V_{DS} = 28 \text{ V}; I_{Dq} = 10 \text{ mA}.$

(1) f = 2400 MHz

(2) f = 2450 MHz

(3) f = 2500 MHz

Fig 3. Power gain and drain efficiency as function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 10 \text{ mA}.$

(1) f = 2400 MHz

(2) f = 2450 MHz

(3) f = 2500 MHz

Fig 4. Power gain and drain efficiency as function of load power; typical values

8. Package outline

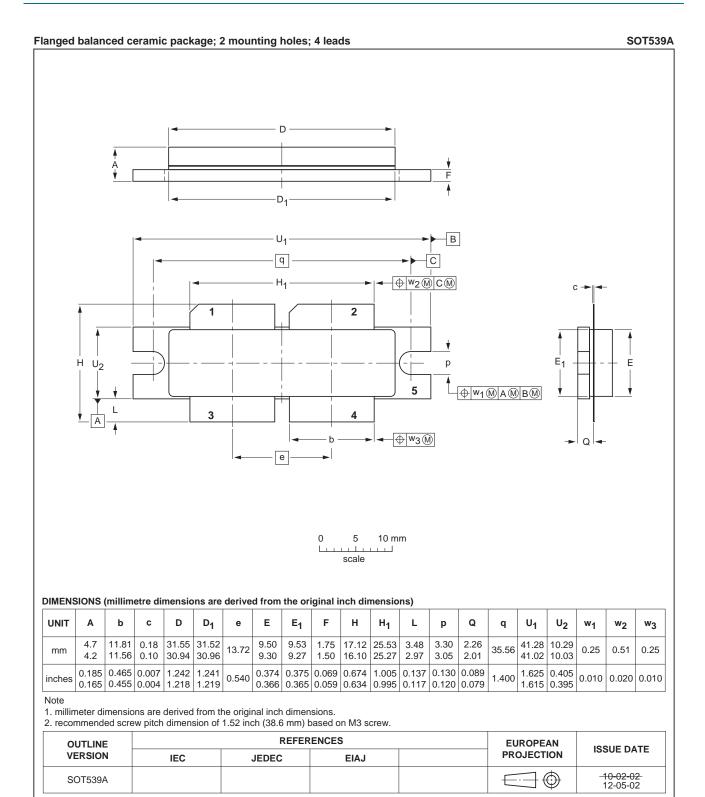


Fig 5. Package outline SOT539A

BLF2425M6L180P_25M6LS180P

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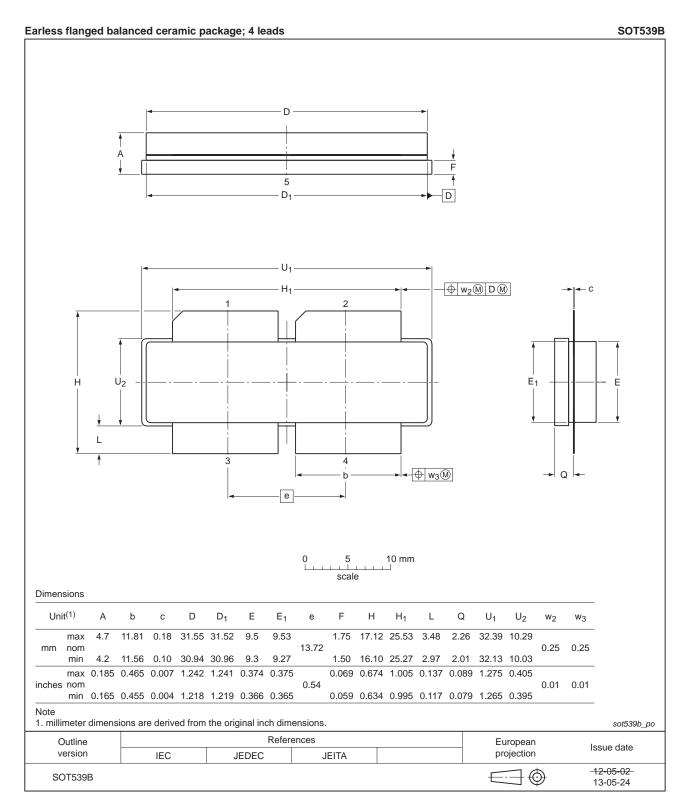


Fig 6. Package outline SOT539B

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

AcronymDescriptionCWContinuous WaveESDElectroStatic DischargeISMIndustrial, Scientific and MedicalLDMOSLaterally Diffused Metal-Oxide SemiconductorSMDSurface Mounted DeviceVSWRVoltage Standing-Wave Ratio		
ESD ElectroStatic Discharge ISM Industrial, Scientific and Medical LDMOS Laterally Diffused Metal-Oxide Semiconductor SMD Surface Mounted Device	Acronym	Description
ISM Industrial, Scientific and Medical LDMOS Laterally Diffused Metal-Oxide Semiconductor SMD Surface Mounted Device	CW	Continuous Wave
LDMOS Laterally Diffused Metal-Oxide Semiconductor SMD Surface Mounted Device	ESD	ElectroStatic Discharge
SMD Surface Mounted Device	ISM	Industrial, Scientific and Medical
2	LDMOS	Laterally Diffused Metal-Oxide Semiconductor
VSWR Voltage Standing-Wave Ratio	SMD	Surface Mounted Device
	VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF2425M6L180P_25M6LS180P v.3	20130712	Product data sheet	-	BLF2425M6L180P_25M6LS180P v.2
Modifications:	The pa	ackage outline Figure	6 is update	ed.
BLF2425M6L180P_25M6LS180P v.2	20120920	Product data sheet	-	BLF2425M6L180P_25M6LS180P v.1
Modifications:	TableSectionTableTableTableSection	atus of this document 1 on page 1: several of in 1.2 on page 1: seve 4 on page 2: an item h 6 on page 3: several of 7 on page 3: several of in 7.1 on page 3: a val in 7.4 on page 6: this s	hanges ha ral change has been re hanges ha hanges ha ue has bee	es have been made. emoved. eve been made. eve been made. eve been made. en added.
BLF2425M6L180P_25M6LS180P v.1	20120207	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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